

## 600V High and Low Side Driver

### PRODUCT SUMMARY

- $V_{\text{OFFSET}}$  600 V max.
- $I_{\text{O}+/-}$  2.5A / 3.5A
- $V_{\text{OUT}}$  10 V - 20 V
- $t_{\text{on/off}}$  (typ.) 180ns / 200ns

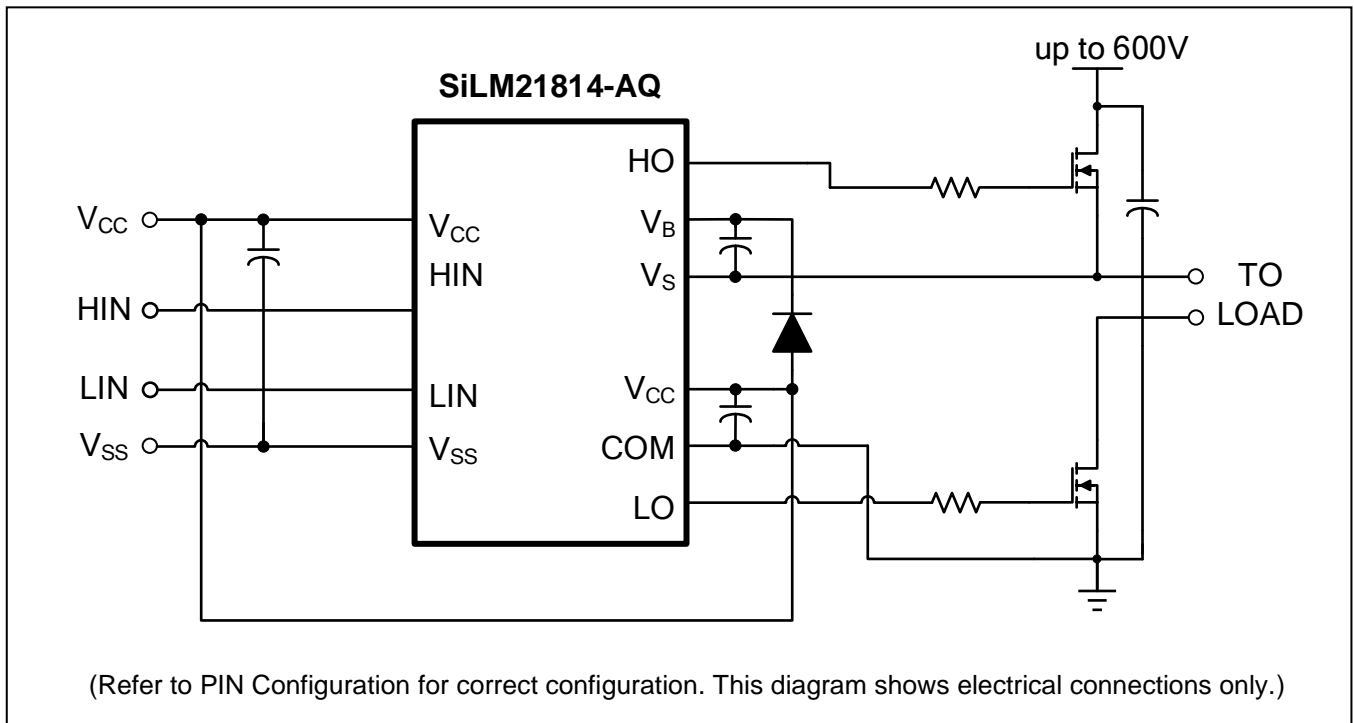
### GENERAL DESCRIPTION

The SiLM21814AQ is a high voltage, high speed power MOSFET and IGBT drivers with independent high- and low-side referenced output channels. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. The logic input is compatible with standard CMOS or LSTTL output, down to 3.3 V logic. The output drivers feature a high pulse current buffer stage designed for minimum driver cross conduction. Propagation delays are matched to simplify use in high frequency applications. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high-side configuration which operates up to 600 V.

### FEATURES

- Floating channel designed for bootstrap operation
- Fully operational to +600 V
- Low  $V_{\text{CC}}$  operation
- Tolerant to negative transient voltage,  $dV/dt$  immune
- Gate drive supply range from 10 V to 20 V
- Undervoltage lockout for both channels
- 3.3 V, and 5 V logic compatible
- CMOS Schmitt-triggered inputs with pull-down
- Matched propagation delay for both channels
- Outputs in phase with inputs
- RoHS compliant
- SOP14 package
- AEC-Q 100 qualified for automotive

### TYPICAL APPLICATION CIRCUIT



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**PIN CONFIGURATION**

Package	Pin Configuration (Top View)
SOP14	

**PIN DESCRIPTION**

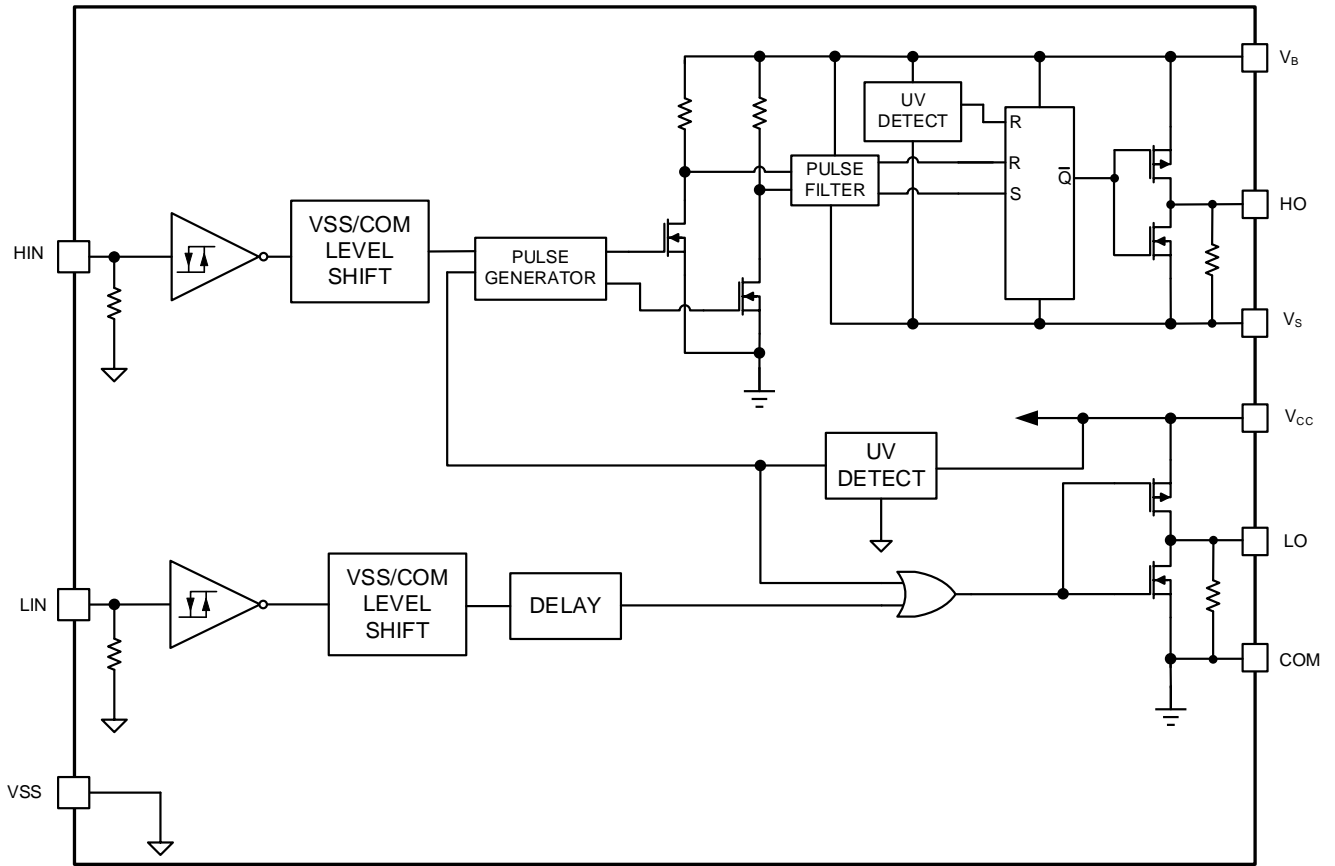
No.	Pin	Description
1	HIN	Logic input for high-side gate driver output (HO), in phase
2	LIN	Logic input for low-side gate driver output (LO), in phase
3	VSS	Logic ground
5	COM	Low-side return
6	LO	Low-side gate drive output
7	V <sub>CC</sub>	Low-side and logic fixed supply
11	V <sub>s</sub>	High-side floating supply return
12	HO	High-side gate drive output
13	V <sub>B</sub>	High-side floating supply
4,8,9,10,14	NC	No Connection

**ORDERING INFORMATION**

Industrial Range: -40°C to +125°C

Order Part No.	Package	QTY
SiLM21814CJ-AQ	SOP14, Pb-Free	2500/Reel

**FUNCTIONAL BLOCK DIAGRAM**



**ABSOLUTE MAXIMUM RATINGS**

Symbol	Definition	Min.	Max.	Units	
V <sub>B</sub>	High-side floating absolute voltage	-0.3	625	V	
V <sub>S</sub>	High-side floating supply offset voltage	V <sub>B</sub> - 25	V <sub>B</sub> + 0.3		
V <sub>HO</sub>	High-side floating output voltage	V <sub>S</sub> - 0.3	V <sub>B</sub> + 0.3		
V <sub>CC</sub>	Low-side and logic fixed supply voltage	-0.3	25		
V <sub>LO</sub>	Low-side output voltage	-0.3	V <sub>CC</sub> + 0.3		
V <sub>IN</sub>	Logic input voltage (HIN & LIN)	V <sub>SS</sub> -0.3	V <sub>SS</sub> + V <sub>CC</sub>		
V <sub>SS</sub>	Logic ground	-5	+5		
dV <sub>S</sub> /dt	Allowable offset supply voltage transient	---	50	V/ns	
P <sub>D</sub>	Package power dissipation @ T <sub>A</sub> ≤ +25°C	SOP14	---	1.0	W
θ <sub>JA</sub>	Thermal resistance, junction to ambient	SOP14	---	120	°C/W
T <sub>J</sub>	Junction temperature	---	150	°C	
T <sub>S</sub>	Storage temperature	-55	150		
T <sub>L</sub>	Lead temperature (soldering, 10 seconds)	---	300		

Note: Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

**RECOMMENDED OPERATION CONDITIONS**

Symbol	Definition	Min	Max	Units
V <sub>B</sub>	High-side floating absolute voltage	V <sub>S</sub> + 10	V <sub>S</sub> + 20	V
V <sub>S</sub>	High-side floating supply offset voltage		600	
V <sub>HO</sub>	High-side floating output voltage	V <sub>S</sub>	V <sub>B</sub>	
V <sub>CC</sub>	Low-side and logic fixed supply voltage	10	20	
V <sub>LO</sub>	Low-side output voltage	0	V <sub>CC</sub>	
V <sub>IN</sub>	Logic input voltage (HIN & LIN)	V <sub>SS</sub>	V <sub>SS</sub> +V <sub>CC</sub>	
T <sub>A</sub>	Ambient temperature	- 40	125	°C

Note: For proper operation the device should be used within the recommended conditions. Logic operational for VS of (COM – 5 V) to (COM + 600V). Logic state held for VS of (COM-5V) to (COM - VBS).

**DYNAMIC ELECTRICAL CHARACTERISTICS**
 $V_{BIAS} (V_{CC}, V_{BS}) = 15\text{ V}$ ,  $C_L = 1000\text{ pF}$  and  $T_A = T_J = -40^\circ\text{C} \sim 125^\circ\text{C}$  unless otherwise specified.

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
$t_{on}$	Turn-on propagation delay	$V_S = 0\text{ V}$	---	180	270	ns
$t_{off}$	Turn-off propagation delay	$V_S = 0\text{ V}$	---	200	300	
$t_r$	Turn-on rise time		---	10	20	
$t_f$	Turn-off fall time		---	8	20	
MT	Delay matching, HS & LS turn-on/off		---	0	35	

**STATIC ELECTRICAL CHARACTERISTICS**
 $V_{BIAS} (V_{CC}, V_{BS}) = 15\text{ V}$ ,  $V_{SS} = \text{COM}$  and  $T_A = T_J = -40^\circ\text{C} \sim 125^\circ\text{C}$  unless otherwise specified. The  $V_{IN}$ ,  $V_{TH}$ , and  $I_{IN}$  parameters are referenced to  $V_{SS}/\text{COM}$  and are applicable to the logic input leads: HIN and LIN. The  $V_O$  and  $I_O$  parameters are referenced to COM and are applicable to the respective output leads: HO and LO.

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
$V_{IH}$	Logic "1" input voltage	$V_{CC} = 10\text{ V to } 20\text{ V}$	2.5	---	---	V
$V_{IL}$	Logic "0" input voltage		---	---	0.8	
$V_{OH}$	High level output voltage, $V_{BIAS} - V_O$	$I_O = 20\text{ mA}$	---	---	0.2	
$V_{OL}$	Low level output voltage, $V_O$		---	0.02	0.15	
$I_{LK}$	Offset supply leakage current	$V_B = V_S = 600\text{ V}$	---	---	50	$\mu\text{A}$
$I_{QBS}$	Quiescent $V_{BS}$ supply current	$V_{IN} = 0\text{ V}$	30	65	100	
$I_{QCC}$	Quiescent $V_{CC}$ supply current		130	270	600	
$I_{IN+}$	Logic "1" input bias current	$HIN=LIN = 5\text{ V}$	---	27	40	
$I_{IN-}$	Logic "0" input bias current	$HIN=LIN = 0\text{ V}$	---	---	5	
$V_{BSUV+}$	$V_{BS}$ supply undervoltage positive going threshold		8.0	8.9	9.8	V
$V_{BSUV-}$	$V_{BS}$ supply undervoltage negative going threshold		7.4	8.2	9.0	
$V_{CCUV+}$	$V_{CC}$ supply undervoltage positive going threshold		8.0	8.9	9.8	V
$V_{CCUV-}$	$V_{CC}$ supply undervoltage negative going threshold		7.4	8.2	9.0	
$I_{O+}$	Output high short circuit pulsed current <sup>1</sup>	$V_O = 0\text{ V}$ $V_{IN} = \text{Logic "1"}$ $PW \leq 10\ \mu\text{s}$		2.5		A
$I_{O-}$	Output low short circuit pulsed current <sup>1</sup>	$V_O = 15\text{ V}$ $V_{IN} = \text{Logic "0"}$ $PW \leq 10\ \mu\text{s}$		3.5		

<sup>1)</sup> Values are verified by characterization on bench.

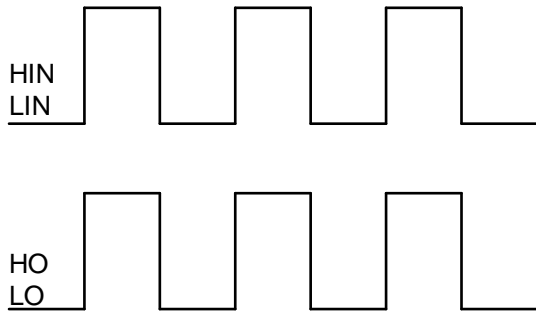


Figure 1. Input/Output Timing Diagram

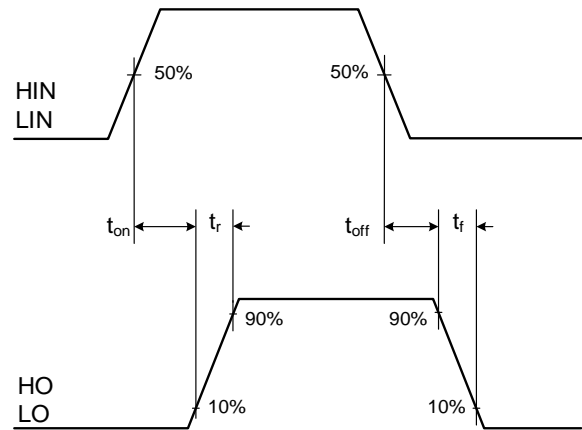


Figure 2. Switching Time Waveform

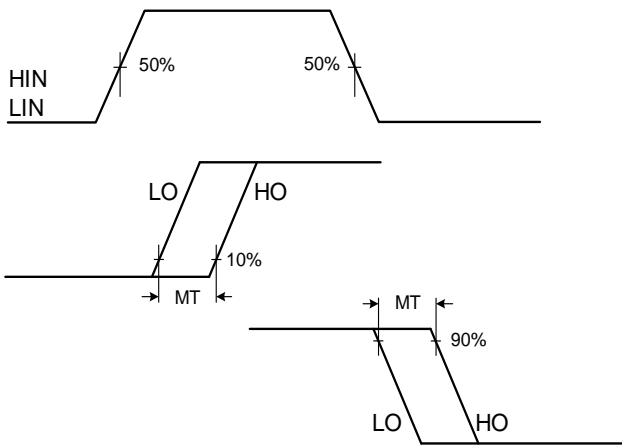


Figure 3. Delay Matching Waveform

## TYPICAL PERFORMANCE CHARACTERISTICS

$V_{BIAS}$  ( $V_{CC}$ ,  $V_{BS}$ ) = 15 V,  $V_{SS}$ =COM and  $T_A$  = 25°C unless otherwise specified.

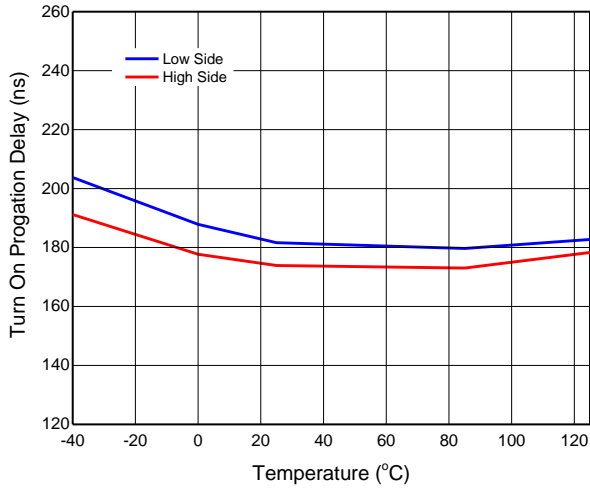


Figure 4. Turn On Delay vs. Temperature

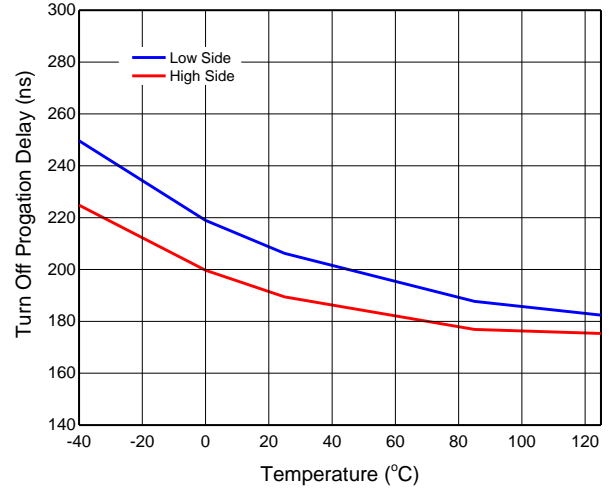


Figure 5. Turn Off Delay vs. Temperature

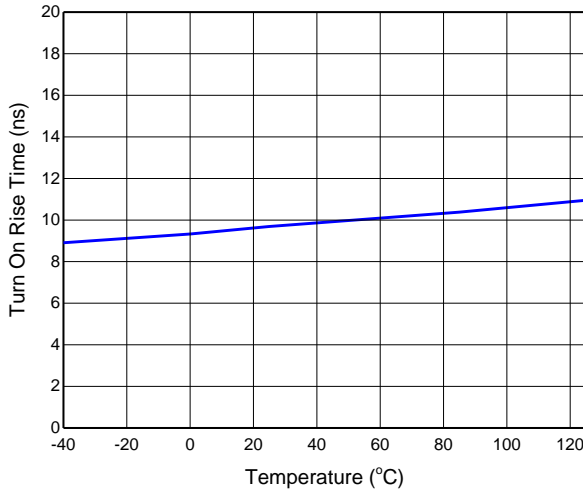


Figure 6. Turn On Rise Time vs. Temperature

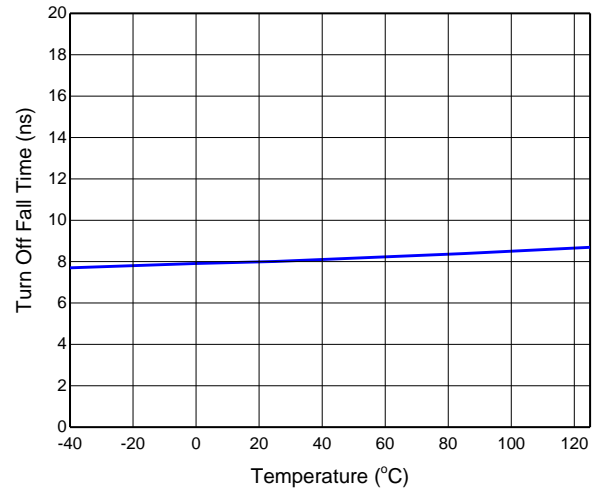


Figure 7. Turn Off Fall Time vs. Temperature

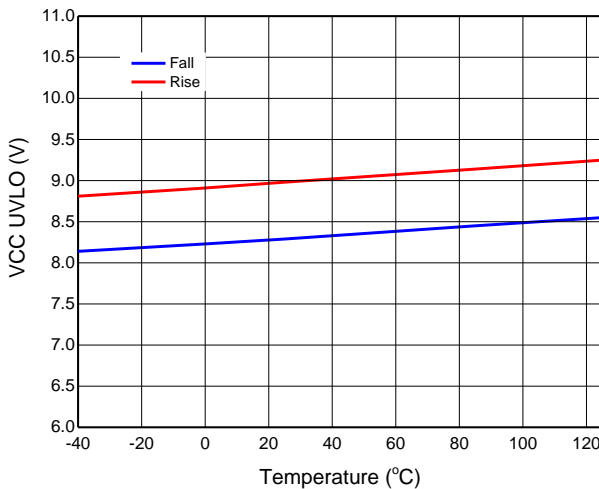


Figure 8. VCC UVLO Threshold vs. Temperature

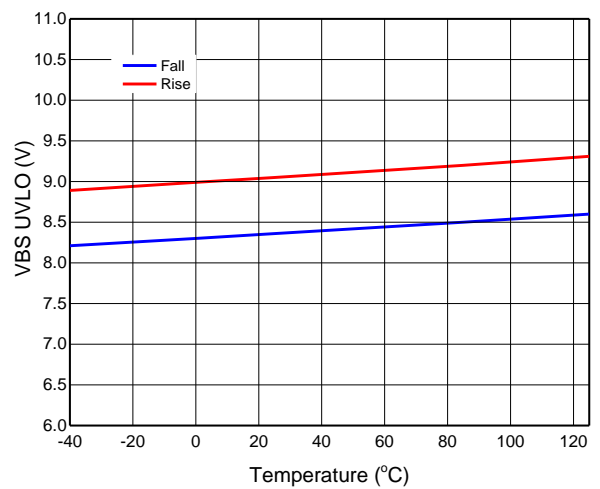


Figure 9. VBS UVLO Threshold vs. Temperature



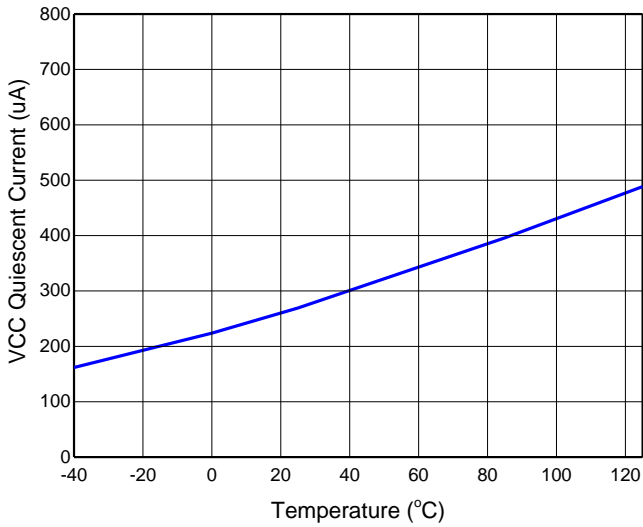


Figure 10. VCC Quiescent Current vs. Temperature

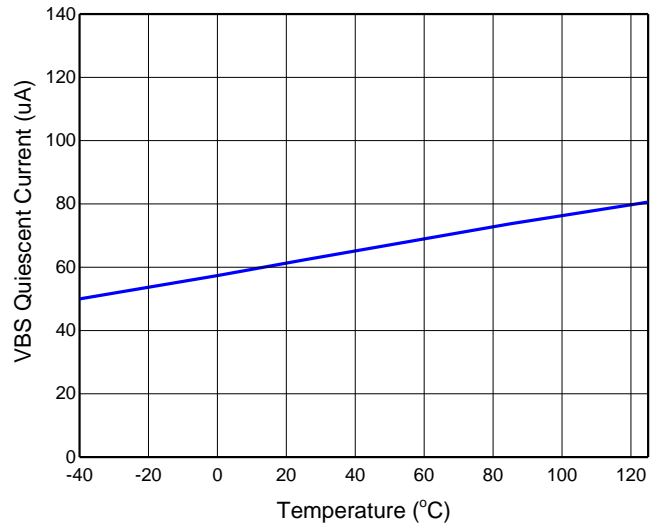


Figure 11. VBS Quiescent Current vs. Temperature

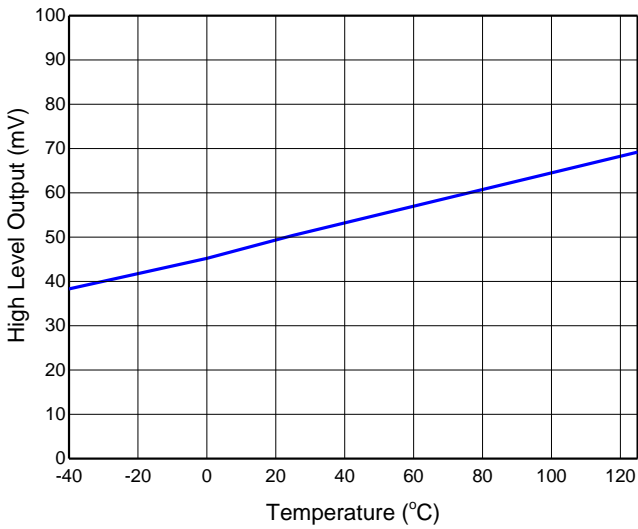


Figure 12. High Level Output vs. Temperature

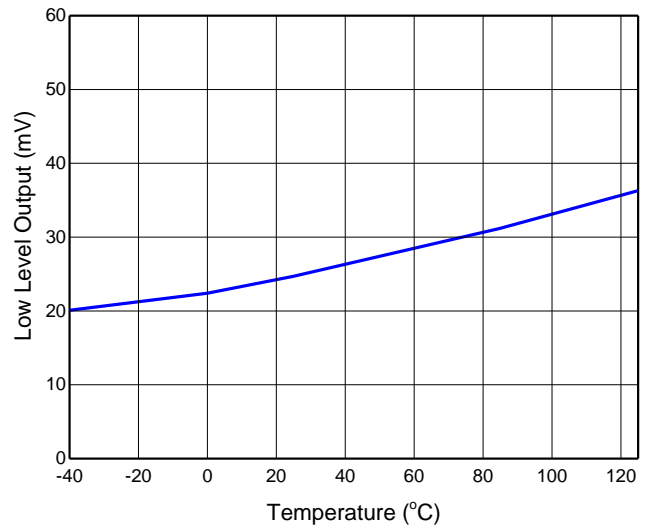


Figure 13. Low Level Output vs. Temperature

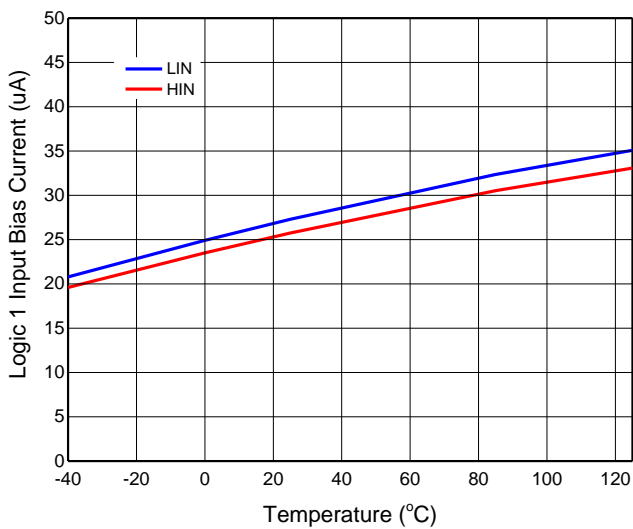


Figure 14. Logic "1" Input Bias Current vs. Temperature

**PACKAGE CASE OUTLINES**

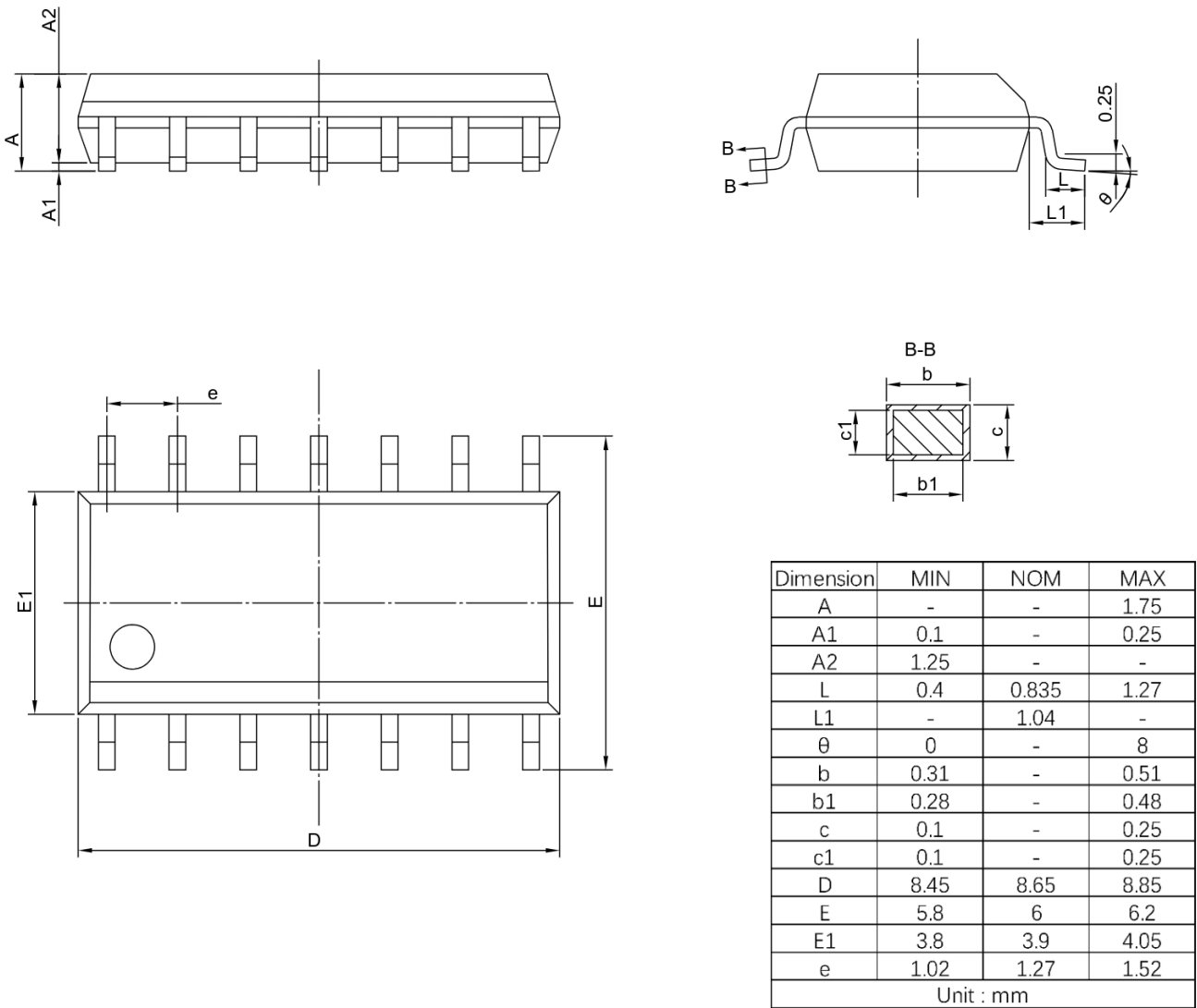


Figure 15. SOP14 Outline Dimensions

**REVISION HISTORY**

Note: page numbers for previous revisions may differ from page numbers in current version

<b>Page or Item</b>	<b>Subjects (major changes since previous revision)</b>
<b>Rev 1.0 datasheet, 2023-07-04</b>	
Whole document	Rev 1.0: Initial Version Release
<b>Rev 1.1 datasheet, 2023-10-23</b>	
Page 6	Revise I <sub>qcc</sub> Max Value from 520μA to 600μA